

03500.017636.

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re Application of:

SHUNICHI ISHIHARA, et al.

Application No.: 10/530,189

Filed: October 10, 2003

For: POLYCRYSTALLINE SILICON  
SUBSTRATE

May 5, 2006

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO-1449. Copies of the listed documents, other than U.S. patent documents, are enclosed.

The following documents are discussed at the following pages of the specification:

<u>Documents</u>	<u>Page(s)</u>
Haruo Itoh, et al., Journal of Crystal Growth	3
T. H. Wang, et al., Solar Energy Materials and Solar Cells	4-5

The Examiner's attention is also directed to the following U.S.

Applications:

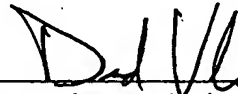
<u>Application No.</u>	<u>Filing Date</u>	<u>Applicant(s)</u>
10/549,600	03/24/2004	S. Ishihara
10/563,115	05/17/2005	M. Mizutani S. Nishida K. Nakagawa
10/976,853	11/01/2004	T. Yoshino S. Nishida

This Information Disclosure Statement is being filed before the issuance of a first Office Action on the merits. Therefore, no fee under 37 C.F.R. § 1.97(c)(2) is believed due. Nevertheless, the Commissioner may charge Deposit Account No. 06-1205, should any fee be due for filing this paper.

Applicants request that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be initialed and returned indicating that such information has been considered.

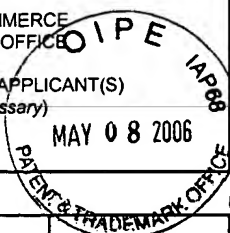
Applicants' undersigned attorney may be reached in our Costa Mesa,  
California office at (714) 540-8700. All correspondence should continue to be directed to  
our below-listed address.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'D. Vadnais', is written over a horizontal line.

Damond E. Vadnais  
Attorney for Applicants  
Registration No.: 52,310

FITZPATRICK, CELLA, HARPER & SCINTO  
30 Rockefeller Plaza  
New York, New York 10112-3800  
Facsimile: (212) 218-2200

FORM PTO 1449 (modified)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)				ATTY DOCKET NO. <b>03500.017636.</b>		APPLICATION NO. <b>10/530,189</b>	
				APPLICANT <b>SHUNICHI ISHIHARA, et al.</b>			
				FILING DATE <b>October 10, 2003</b>		GROUP	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,953,506	10/11/05	Iwane, et al.	117	206	
		6,869,863	03/22/05	Nishida	438	497	
		6,824,609	11/30/04	Saito, et al.	117	54	
		6,818,911	11/16/04	Tamamori, et al.	250	492.22	
		6,818,104	11/16/04	Iwasaki, et al.	204	199	
		6,802,926	10/12/04	Mizutani, et al.	156	247	
		6,802,900	10/12/04	Iwane, et al.	117	54	
		6,756,289	06/29/04	Nakagawa, et al.	438	478	
		6,802,990	01/27/04	Iwane, et al.	438	458	
		6,664,169	12/16/03	Iwasaki, et al.	438	409	
		6,653,554	11/25/03	Ishihara	136	258	
		6,566,277	05/20/03	Nakagawa, et al.	438	761	
		6,566,235	05/20/03	Nishida, et al.	438	458	
		6,515,218	02/04/03	Shimizu, et al.	136	256	
		6,500,731	12/31/02	Nakagawa, et al.	438	455	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT- NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)							
		Haruo Itoh, et al., "Characterization of Silicon Layers Epitaxially Grown on Metallurgical-Grade Polycrystalline Substrates", Journal of Crystal Growth 45 (1978), pp. 446-453.					
		T. H. Wang, et al., "Growth of silicon thin layers on cast MG-Si from metal solutions for solar cells", Solar Energy Materials and Solar Cells 41/42 (1996), pp. 19-30.					
EXAMINER				DATE CONSIDERED			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,464,762	10/15/02	Arao	106	1.22	
		6,452,091	09/17/02	Nakagawa, et al.	136	261	
		6,429,035	08/06/02	Nakagawa, et al.	438	57	
		6,391,743	05/21/02	Iwane, et al.	438	458	
		6,387,780	05/14/02	Nishida, et al.	438	497	
		6,384,313	05/07/02	Nakagawa, et al.	136	244	
		6,331,208	12/18/01	Nishida, et al.	117	89	
		6,271,462	08/07/01	Tsuzuki, et al.	438	290	
		6,265,242	07/24/01	Komori, et al.	438	66	
		6,258,698	07/10/01	Iwasaki, et al.	438	455	
		6,258,666	07/10/01	Mizutani, et al.	438	258	
		6,248,948	06/19/01	Nakagawa, et al.	136	244	
		6,211,038	04/03/01	Nakagawa, et al.	438	458	
		6,190,937	02/20/01	Nakagawa, et al.	438	67	
		6,184,458	02/06/01	Murakami, et al.	136	256	
		6,180,868	01/30/01	Yoshino, et al.	136	244	
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Sheet 2 of 3

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		6,172,296	01/09/01	Iwasaki, et al.	136	256	
		6,162,986	12/19/00	Shiotsuka, et al.	136	244	
		6,140,209	10/31/00	Iwane, et al.	438	458	
		6,110,347	08/29/00	Arao, et al.	205	333	
		5,986,204	11/16/99	Iwasaki, et al.	136	256	
		5,981,864	11/09/99	Mizutani, et al.	136	244	
		5,770,463	06/23/98	Nakagawa, et al.	437	2	
		5,714,010	02/03/98	Matsuyama, et al.	117	723	
		5,712,199	01/27/98	Nakagawa, et al.	438	62	
		5,510,151	04/23/96	Matsuyama, et al.	427	509	
		5,486,238	01/23/96	Nakagawa, et al.	136	259	
		2005/0136576	06/23/05	Ishihara, et al.	438	162	
		2005/0109388	05/26/05	Murakami, et al.	136	255	
		2005/0087226	04/28/05	Nishida, et al.	136	256	
		2005/0066881	03/31/05	Nakagawa, et al.	117	18	
		2004/0118337	06/24/04	Mizutani, et al.	117	54	
		2004/0065251	04/08/04	Nishida, et al.	117	54	
		2002/0092464	07/18/02	Nakagawa, et al.	117	94	

FOREIGN PATENT DOCUMENTS							
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Sheet 3 of 3